

197261US-2



101A
5-23-02
R. Dinkler

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

Shusuke KAYA ET AL.

SERIAL NO: 09/662,704

FILED: SEPTEMBER 15, 2000

FOR: SEMICONDUCTOR LASER DEVICE

:

: EXAMINER: HARMON, C.

:

: GROUP ART UNIT: 2881

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated January 15, 2002, please amend the above-identified application as follows.

IN THE CLAIMS

Please amend Claims 2 and 17 as follows:

a1 2. (Amended) The semiconductor laser device according to claim 19, wherein said low reflection film is formed from a single layer.

a2 17. (Amended) The semiconductor laser device according to any one of claims 1 to 16, wherein said Al_2O_3 film is deposited by an electron cyclotron resonance plasma sputtering process.

Please add new Claims 18 and 19 as follows:

a3 18. (New) A semiconductor laser device comprising:

a semiconductor multi-layer film comprising at least one confinement layer and at least one active layer;

RECEIVED
MAY 17 2002
TECHNOLOGY CENTER 2800